

**PATENT**

## Applicant: Kie Y. Ahn et al.

Examiner: Unknown

Serial No.: Unknown

Group Art Unit: Unknown

Filed:                      Herewith

Docket: 303.377US3

Title: POROUS SILICON OXYCARBIDE INTEGRATED CIRCUIT INSULATOR

#3/a  
1/3-01  
Payton

## BOX PATENT APPLICATION

Commissioner for Patents

Washington, D.C. 20231

Sir:

Prior to taking up the above-identified patent application for review, please amend the application as follows:

On page 1, line 5, before the heading, "Technical Field of the Invention", insert the following paragraph:

### **Cross Reference to Related Applications**

This application is a continuation of U.S. Patent Application No. 08/950,319, filed on October 14, 1997, the specification of which is incorporated herein by reference.

## IN THE CLAIMS

Please cancel claims 1 - 48 without prejudice or disclaimer.

Please add new claims 49 - 80.

49. A method, comprising:  
forming a plurality of circuit elements on a substrate;  
coating at least a portion of a surface of the substrate and at least one of the plurality of circuit elements with a mixture of oxide and carbon sources; and  
transforming the mixture of oxide and carbon sources into a silicon oxycarbide having uniformly distributed voids that have an approximate diameter between 20 angstroms and 300 angstroms and which has a dielectric constant less than approximately 2.0.